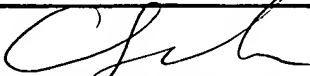


1449A/PTO Rev. 10/95		U.S. Department of Commerce Patent and Trademark Office		Complete If Known	
LIST OF PRIOR ART CITED BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/ 780, 929
				Filing Date	February 17, 2004
				First Named Inventor	DOUGLAS JAMES TWEET
				Group Art Unit	
				Examiner Name	
Sheet	1	of	2	Attorney Docket No.	SLA.0735

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	U.S. Patent Document Kind Number	Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YY	Pages, Columns, Lines, Where Relevant Passages or Figures Appear
CAL		6,464,780	B1	Mantl et al.	10-15-02	
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		Office Code ³	Number ⁴	Kind				

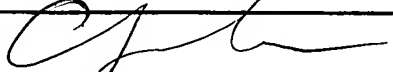
OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T ²

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
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